

FQB12N50 / FQI12N50

500V N-Channel MOSFET

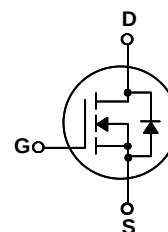
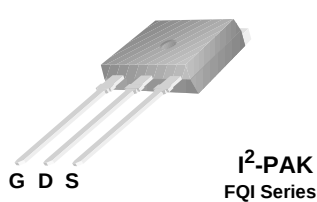
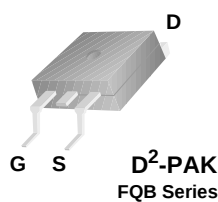
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies, power factor correction, electronic lamp ballasts based on half bridge.

Features

- 12.1A, 500V, $R_{DS(on)} = 0.49\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 39 nC)
- Low C_{rss} (typical 25 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB12N50 / FQI12N50	Units
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	12.1	A
	- Continuous ($T_C = 100^\circ\text{C}$)	7.6	A
I_{DM}	Drain Current - Pulsed (Note 1)	48.4	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	878	mJ
I_{AR}	Avalanche Current (Note 1)	12.1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	17.9	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	179	W
	- Derate above 25°C	1.43	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.48	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 6.05\text{ A}$ (Note 4)	--	0.39	0.49	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 6.05\text{ A}$	--	9.8	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1550	2020	pF
C_{oss}	Output Capacitance		--	220	285	pF
C_{rss}	Reverse Transfer Capacitance		--	25	33	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 12.1\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4,5)	--	35	80	ns
t_r	Turn-On Rise Time		--	120	250	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	150	ns
t_f	Turn-Off Fall Time		--	80	170	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 12.1\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4,5)	--	39	51	nC
Q_{gs}	Gate-Source Charge		--	9.3	--	nC
Q_{gd}	Gate-Drain Charge		--	17.4	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12.1	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48.4	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 12.1 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 12.1 A,	--	300	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	2.6	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 10.8\text{ mH}$, $I_{AS} = 12.1\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 12.1\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

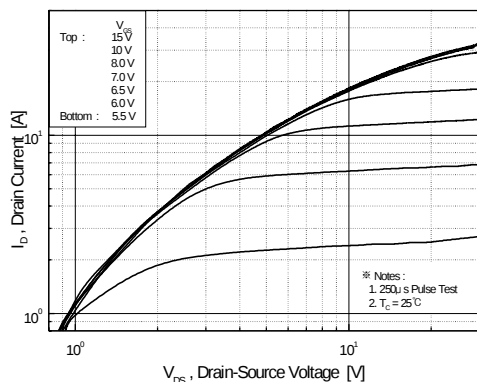


Figure 1. On-Region Characteristics

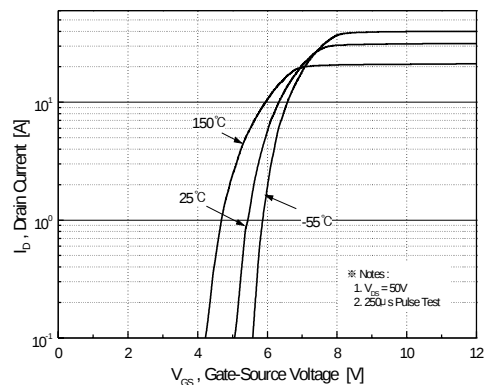


Figure 2. Transfer Characteristics

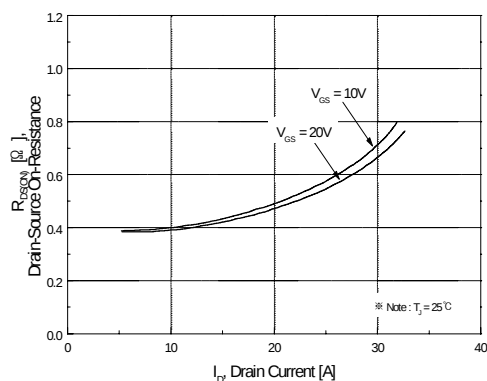


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

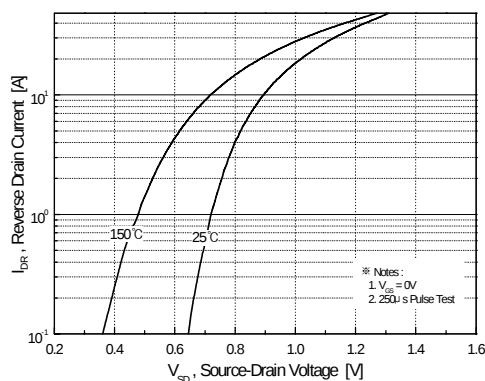


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

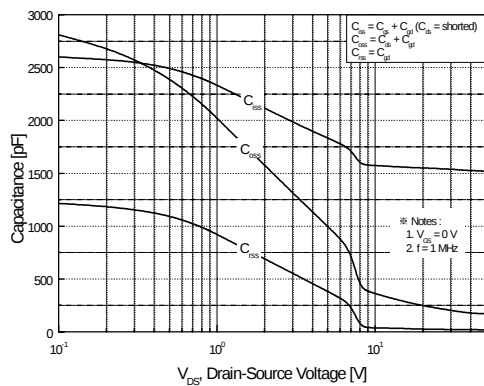


Figure 5. Capacitance Characteristics

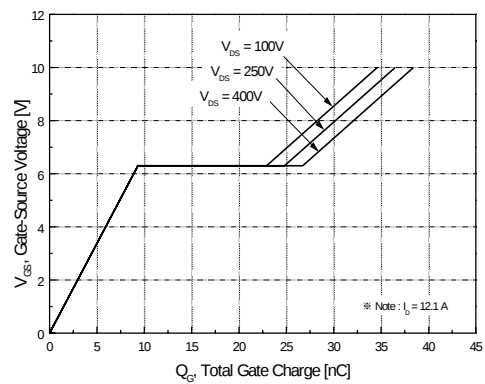


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

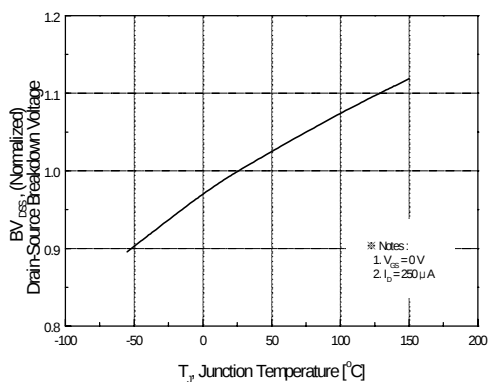


Figure 7. Breakdown Voltage Variation vs. Temperature

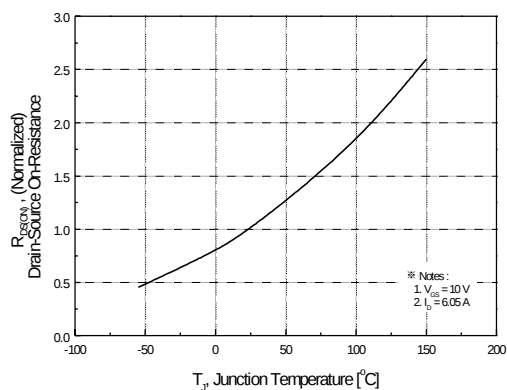


Figure 8. On-Resistance Variation vs. Temperature

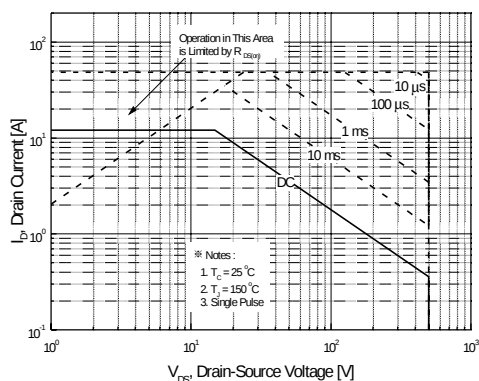


Figure 9. Maximum Safe Operating Area

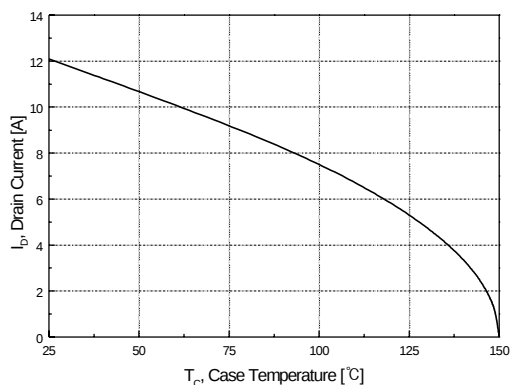


Figure 10. Maximum Drain Current vs. Case Temperature

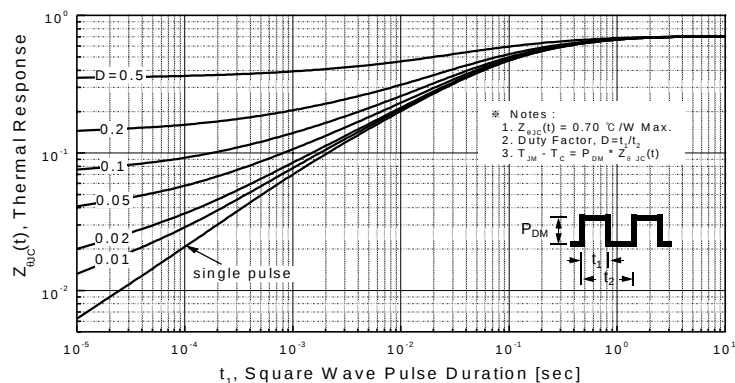
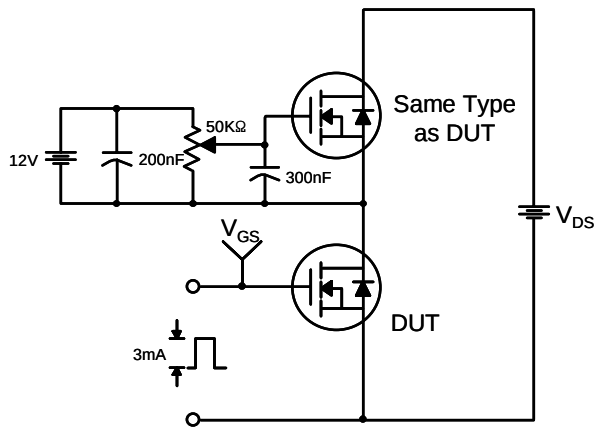


Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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Technical drawing of a 10-pin D-sub connector showing front, side, and top views with dimensions in millimeters.

Front View Dimensions:

- Overall Width: 9.90 ± 0.20
- Overall Height: 15.30 ± 0.30
- Pin Height (from base): 4.90 ± 0.20
- Pin Spacing (center-to-center): 2.54 TYP
- Pin Diameter: 0.80 ± 0.10
- Pin Length (from base): 1.27 ± 0.10
- Pin Thickness: 1.40 ± 0.20
- Pin Spacing (from centerline): 1.27 ± 0.10
- Pin Thickness (from base): 1.20 ± 0.20
- Pin Thickness (from base): 9.20 ± 0.20
- Pin Thickness (from base): 1.20 ± 0.20

Side View Dimensions:

- Overall Width: 4.50 ± 0.20
- Overall Height: 15.30 ± 0.30
- Pin Height (from base): 4.90 ± 0.20
- Pin Spacing (center-to-center): 2.54 ± 0.30
- Pin Diameter: 0.80 ± 0.10
- Pin Length (from base): 1.27 ± 0.10
- Pin Thickness: 1.40 ± 0.20
- Pin Spacing (from centerline): 1.27 ± 0.10
- Pin Thickness (from base): 1.20 ± 0.20
- Pin Thickness (from base): 9.20 ± 0.20
- Pin Thickness (from base): 1.20 ± 0.20

Top View Dimensions:

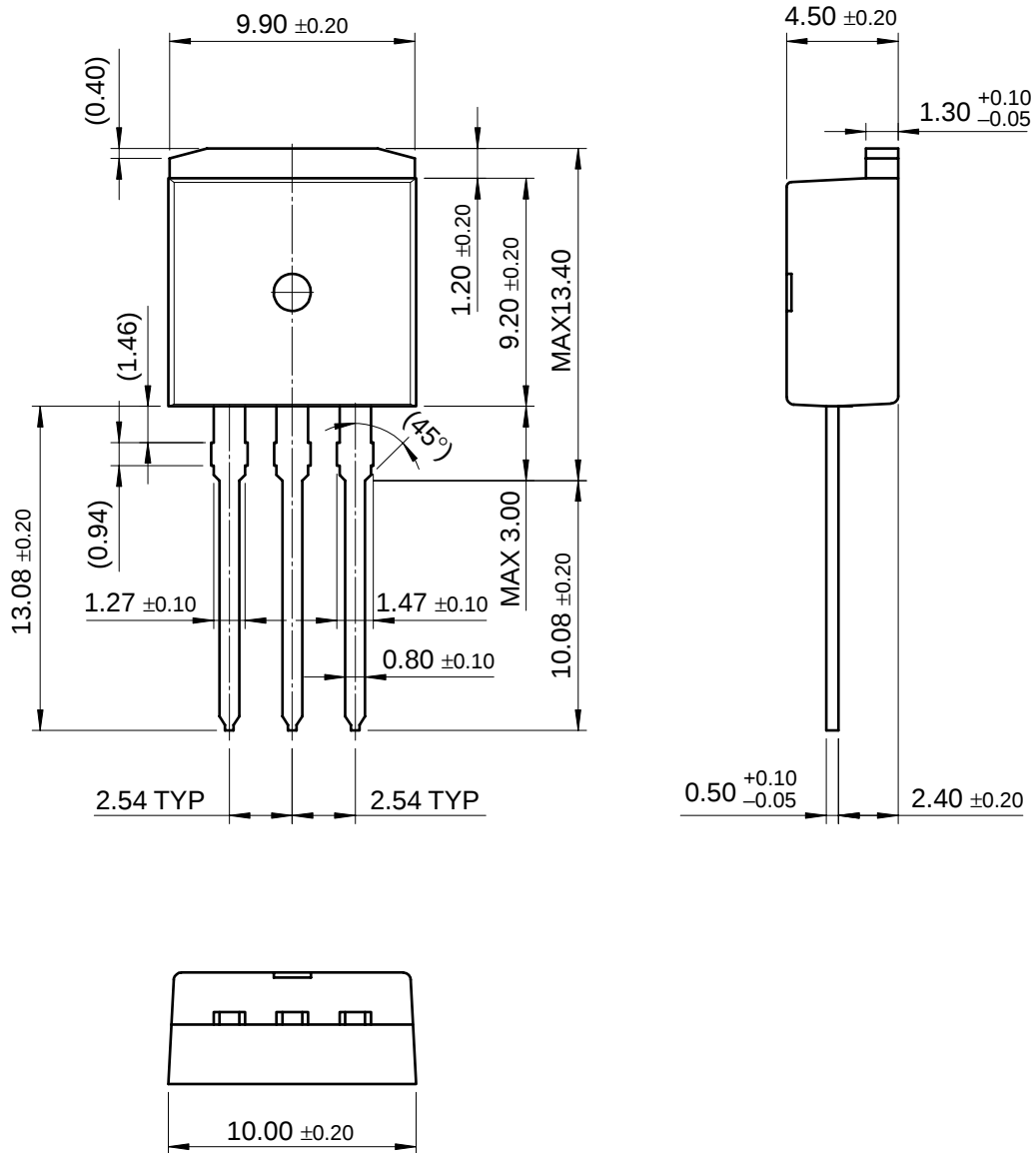
- Overall Width: 10.00 ± 0.20
- Overall Height: 15.30 ± 0.30
- Pin Height (from base): 4.90 ± 0.20
- Pin Spacing (center-to-center): 2.54 ± 0.30
- Pin Diameter: 0.80 ± 0.10
- Pin Length (from base): 1.27 ± 0.10
- Pin Thickness: 1.40 ± 0.20
- Pin Spacing (from centerline): 1.27 ± 0.10
- Pin Thickness (from base): 1.20 ± 0.20
- Pin Thickness (from base): 9.20 ± 0.20
- Pin Thickness (from base): 1.20 ± 0.20

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Package Dimensions (Continued)

I²PAK



Dimensions in Millimeters

FQI12N50 / FQI12N50

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